

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

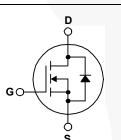
ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or unavteries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor and is officers, employees, uniotificated use, even if such claim any manner.



N-Channel QFET[®] MOSFET 150 V, 50 A, 42 mΩ

Features

- + 50 A, 150 V, ${\sf R}_{{\sf DS}({\sf on})}$ = 42 m Ω (Max) @V_{{\sf GS}} = 10 V, I_D = 25 A
- Low Gate Charge (Typ. 85 nC)
- Low Crss (Typ. 100 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



control, and variable switching power applications.

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar

stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state

resistance, and to provide superior switching performance and

high avalanche energy strength. These devices are suitable for

switched mode power supplies, audio amplifier, DC motor

Description

Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQA46N15	Unit	
V _{DSS}	Drain-Source Voltage		150	V	
I _D	Drain Current - Continuous ($T_c = 25^{\circ}C$)		50	А	
	- Continuous (T _C = 100°C)		35.3	А	
DM	Drain Current - Pulsed	(Note 1)	200	А	
V _{GSS}	Gate-Source Voltage		± 25	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	650	mJ	
AR	Avalanche Current	(Note 1)	50	A	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	25	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns	
P _D	Power Dissipation ($T_C = 25^{\circ}C$)		250	W	
	- Derate above 25°C		1.67	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C	

TO-3PN

Thermal Characteristics

Symbol	Parameter	FQA46N15	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.6	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

Package	Marking	and	Ordering	Information
i uonugo	manning	ana	Craoring	mornation

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQA46N15	FQA46N15	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I _D = 250 μ A	150			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu A$, Referenced to 25°C		0.16		V/°C
I _{DSS} Zer	Zero Gate Voltage Drain Current	V _{DS} = 150 V, V _{GS} = 0 V			1	μA
		V _{DS} = 120 V, T _C = 150°C			10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 25 V, V_{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -25 V, V_{DS} = 0 V			-100	nA
On Charact	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 25A		0.033	0.042	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 25A		36		S
Dynamic Cl	haracteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		2500	3250	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		520	670	pF
C _{rss}	Reverse Transfer Capacitance			100	130	pF
Switching C	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 75 V, I _D = 45.6A,		35	80	ns
t _r	Turn-On Rise Time	- R _G = 25 Ω 		320	650	ns
t _{d(off)}	Turn-Off Delay Time			210	430	ns
t _f	Turn-Off Fall Time	(Note 4)		200	410	ns
Qg	Total Gate Charge	V _{DS} = 120 V, I _D = 45.6A,		85	110	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		15		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	-	41		nC
Drain-Source	ce Diode Characteristics and Maximum Ratings	3			/	
I _S	Maximum Continuous Drain-Source Diode Forward Current				50	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				200	А
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S =50A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 45.6 A,		130		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		0.55		μC

NOTES:

1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. L = 0.43 mH, I_{AS} = 50 A, V_{DD} = 25 V, R_G = 25 $\Omega,$ starting T_J = 25°C.

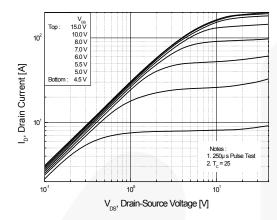
 $3.I_{SD} \leq 46.6$ A, di/dt ≤ 300 A/µs, $V_{DD} \leq BV_{DSS},$ starting T_J = 25°C.

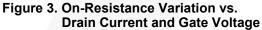
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics



Figure 2. Transfer Characteristics





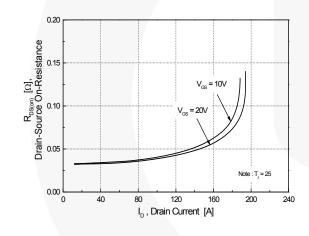
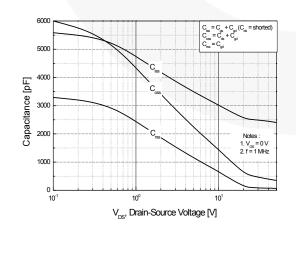
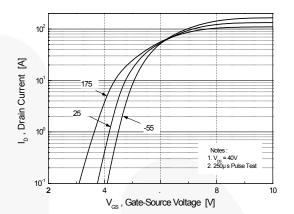
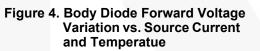
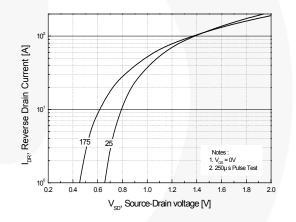


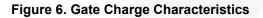
Figure 5. Capacitance Characteristics

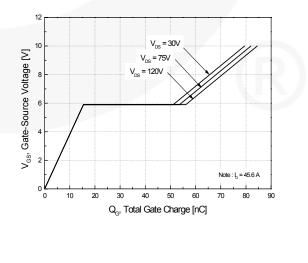


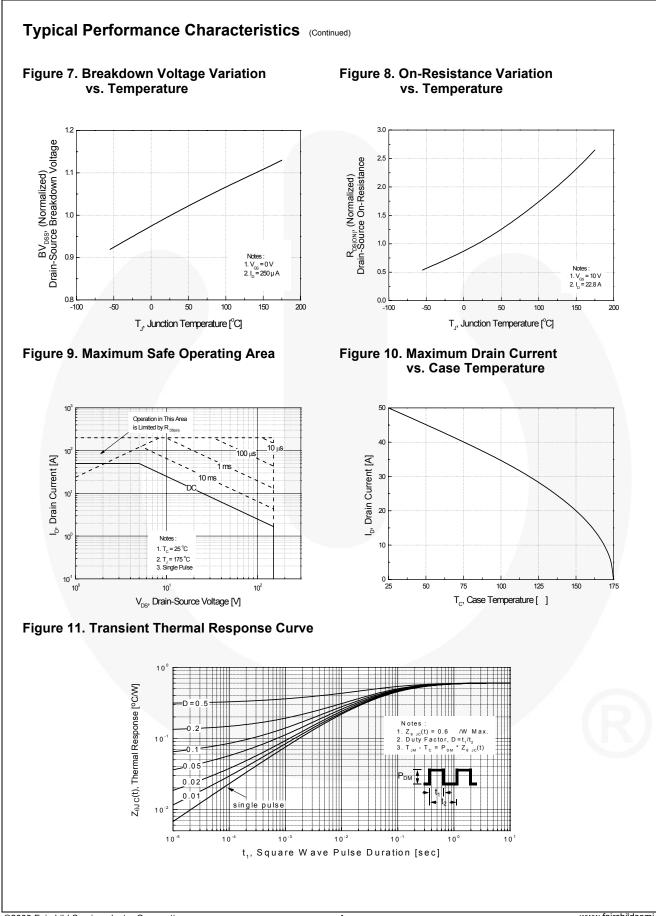






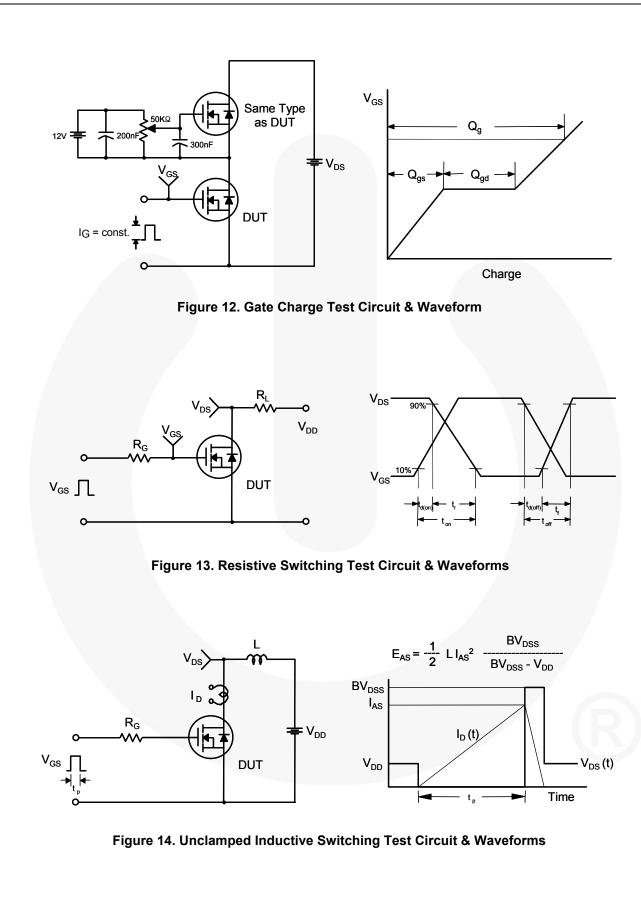


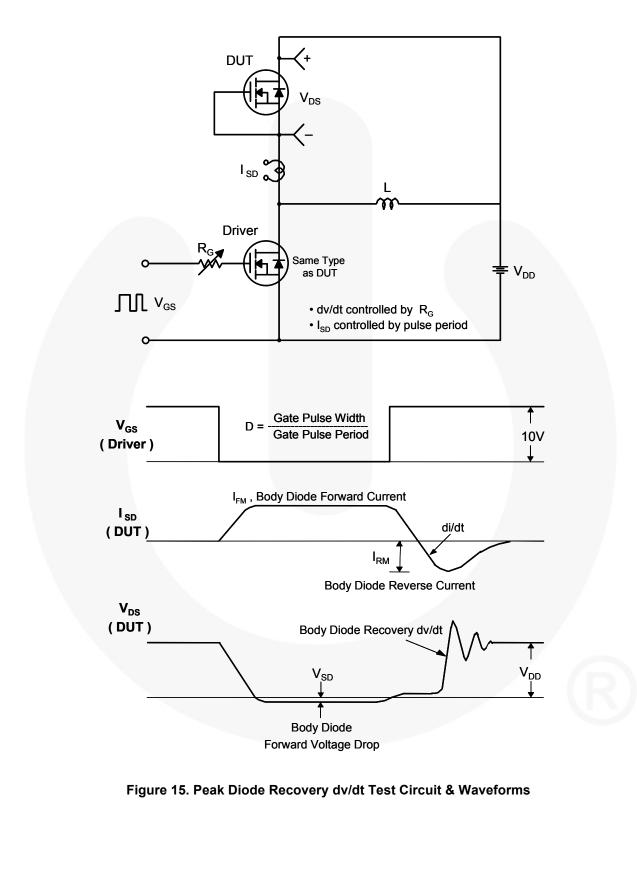


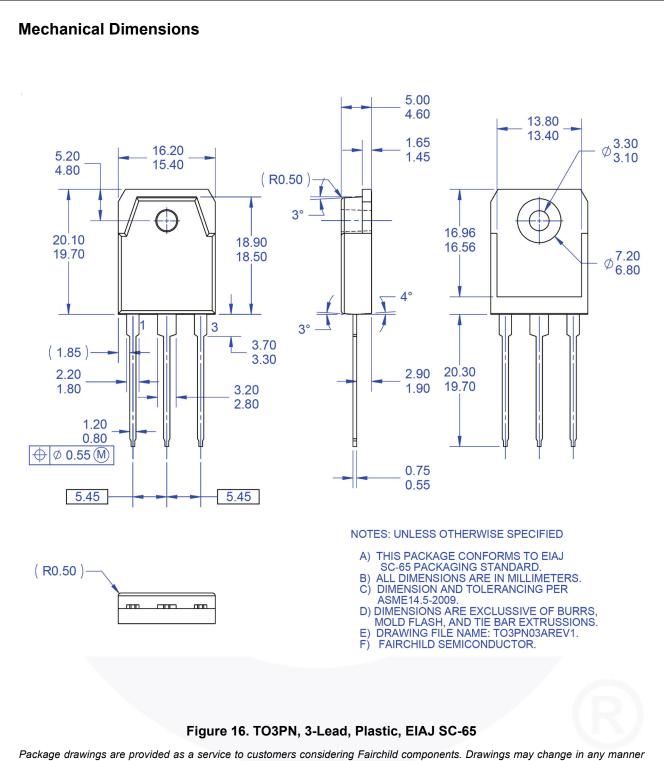


4

FQA46N15 — N-Channel QFET[®] MOSFET







Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT3PN-003

FQA46N15 — N-Channel QFET[®] MOSFET



Not In Production

Obsolete

Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC